



3.3V CMOS 16-BIT BUFFER/DRIVER WITH 3-STATE OUTPUTS

IDT74ALVC16244A

FEATURES:

- 0.5 MICRON CMOS Technology
- Typical $t_{sk(o)}$ (Output Skew) < 250ps
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- $V_{CC} = 3.3V \pm 0.3V$, Normal Range
- $V_{CC} = 2.7V$ to $3.6V$, Extended Range
- $V_{CC} = 2.5V \pm 0.2V$
- CMOS power levels ($0.4\mu W$ typ. static)
- Rail-to-Rail output swing for increased noise margin
- Available in TSSOP package

DRIVE FEATURES:

- High Output Drivers: $\pm 24mA$
- Suitable for heavy loads

DESCRIPTION:

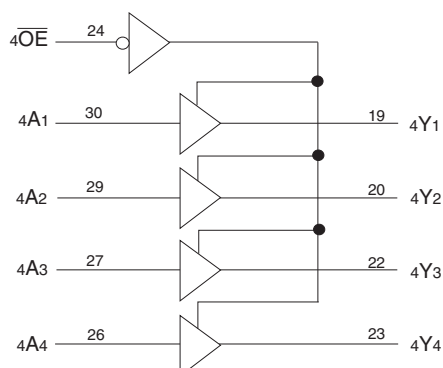
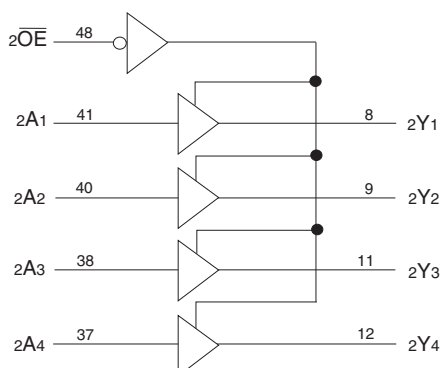
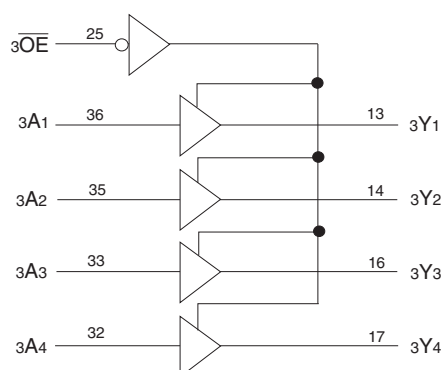
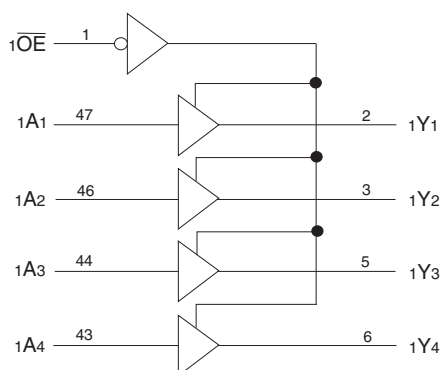
This 16-bit buffer/driver is built using advanced dual metal CMOS technology. The ALVC16244A is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

The ALVC16244A has been designed with a $\pm 24mA$ output driver. This driver is capable of driving a moderate to heavy load while maintaining speed performance.

APPLICATIONS:

- 3.3V high speed systems
- 3.3V and lower voltage computing systems

FUNCTIONAL BLOCK DIAGRAM

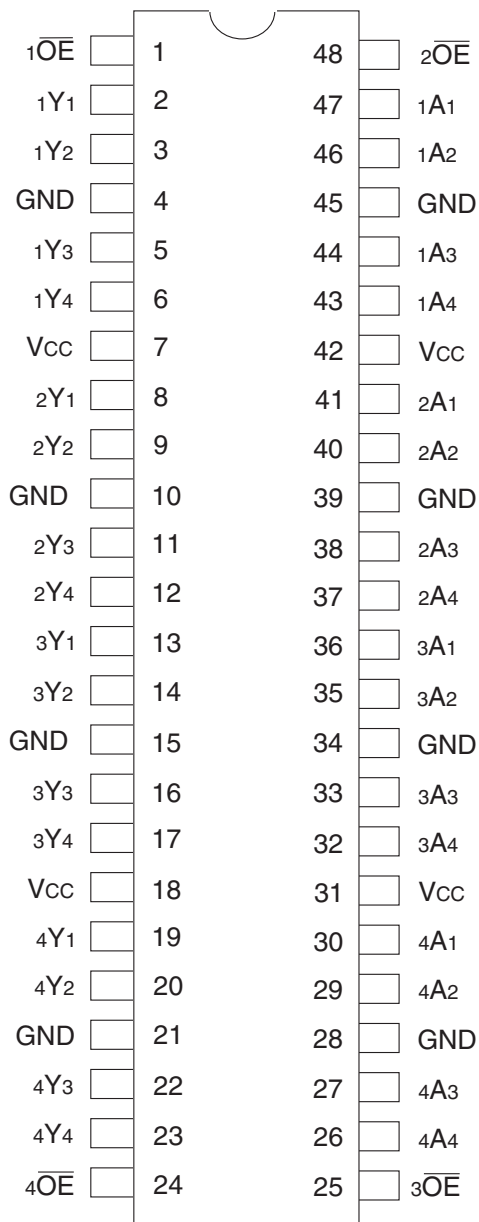


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INDUSTRIAL TEMPERATURE RANGE

JUNE 2016

PIN CONFIGURATION



TSSOP
TOP VIEW

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to VCC+0.5	V
TSTG	Storage Temperature	-65 to +150	°C
IOUT	DC Output Current	-50 to +50	mA
IIK	Continuous Clamp Current, VI < 0 or VI > VCC	±50	mA
IOK	Continuous Clamp Current, VO < 0	-50	mA
ICC ISS	Continuous Current through each VCC or GND	±100	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VCC terminals.
- All terminals except VCC.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	5	7	pF
COUT	Output Capacitance	VOUT = 0V	7	9	pF
COUT	I/O Port Capacitance	VIN = 0V	7	9	pF

NOTE:

- As applicable to the device type.

PIN DESCRIPTION

Pin Names	Description
xOE	3-State Output Enable Inputs (Active LOW)
xAx	Data Inputs
XYx	3-State Outputs

FUNCTION TABLE⁽¹⁾

Inputs		Outputs
xOE	xAx	XYx
L	H	H
L	L	L
H	X	Z

NOTE:

- H = HIGH Voltage Level
X = Don't Care
L = LOW Voltage Level
Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Operating Condition: $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$

Symbol	Parameter	Test Conditions		Min.	Typ. ⁽¹⁾	Max.	Unit
V_{IH}	Input HIGH Voltage Level	$V_{CC} = 2.3\text{V}$ to 2.7V		1.7	—	—	V
		$V_{CC} = 2.7\text{V}$ to 3.6V		2	—	—	
V_{IL}	Input LOW Voltage Level	$V_{CC} = 2.3\text{V}$ to 2.7V		—	—	0.7	V
		$V_{CC} = 2.7\text{V}$ to 3.6V		—	—	0.8	
I_{IH}	Input HIGH Current	$V_{CC} = 3.6\text{V}$	$V_I = V_{CC}$	—	—	± 5	μA
I_{IL}	Input LOW Current	$V_{CC} = 3.6\text{V}$	$V_I = \text{GND}$	—	—	± 5	μA
I_{OZH}	High Impedance Output Current (3-State Output pins)	$V_{CC} = 3.6\text{V}$	$V_O = V_{CC}$	—	—	± 10	μA
I_{OZL}			$V_O = \text{GND}$	—	—	± 10	
V_{IK}	Clamp Diode Voltage	$V_{CC} = 2.3\text{V}$, $I_{IN} = -18\text{mA}$		—	-0.7	-1.2	V
V_H	Input Hysteresis	$V_{CC} = 3.3\text{V}$		—	100	—	mV
I_{CCL} I_{CCH} I_{CCZ}	Quiescent Power Supply Current	$V_{CC} = 3.6\text{V}$ $V_{IN} = \text{GND}$ or V_{CC}		—	0.1	40	μA
ΔI_{CC}	Quiescent Power Supply Current Variation	One input at $V_{CC} - 0.6\text{V}$, other inputs at V_{CC} or GND		—	—	750	μA

NOTE:

1. Typical values are at $V_{CC} = 3.3\text{V}$, $+25^{\circ}\text{C}$ ambient.

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	$V_{CC} = 2.3\text{V}$ to 3.6V	$I_{OH} = -0.1\text{mA}$	$V_{CC} - 0.2$	—	V
		$V_{CC} = 2.3\text{V}$	$I_{OH} = -6\text{mA}$	2	—	
		$V_{CC} = 2.3\text{V}$	$I_{OH} = -12\text{mA}$	1.7	—	
		$V_{CC} = 2.7\text{V}$		2.2	—	
		$V_{CC} = 3\text{V}$		2.4	—	
		$V_{CC} = 3\text{V}$	$I_{OH} = -24\text{mA}$	2	—	
V_{OL}	Output LOW Voltage	$V_{CC} = 2.3\text{V}$ to 3.6V	$I_{OL} = 0.1\text{mA}$	—	0.2	V
		$V_{CC} = 2.3\text{V}$	$I_{OL} = 6\text{mA}$	—	0.4	
			$I_{OL} = 12\text{mA}$	—	0.7	
		$V_{CC} = 2.7\text{V}$	$I_{OL} = 12\text{mA}$	—	0.4	
		$V_{CC} = 3\text{V}$	$I_{OL} = 24\text{mA}$	—	0.55	

NOTE:

1. V_{IH} and V_{IL} must be within the min. or max. range shown in the DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE table for the appropriate V_{CC} range.
 $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$.

OPERATING CHARACTERISTICS, $T_A = 25^\circ\text{C}$

Symbol	Parameter	Test Conditions	$V_{CC} = 2.5V \pm 0.2V$	$V_{CC} = 3.3V \pm 0.3V$	Unit
			Typical	Typical	
CPD	Power Dissipation Capacitance Outputs enabled	$C_L = 0\text{pF}$, $f = 10\text{MHz}$	16	19	pF
CPD	Power Dissipation Capacitance Outputs disabled		4	5	

SWITCHING CHARACTERISTICS⁽¹⁾

Symbol	Parameter	$V_{CC} = 2.5V \pm 0.2V$		$V_{CC} = 2.7V$		$V_{CC} = 3.3V \pm 0.3V$		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay xA to xBx	1	4.4	—	4	1	3.6	ns
t_{PZH} t_{PZL}	Output Enable Time $\overline{OE}$ to xBx	1	6.3	—	6	1	5	ns
t_{PHZ} t_{PLZ}	Output Disable Time $\overline{OE}$ to xBx	1	5.8	—	5.2	1	5	ns
$t_{SK(O)}$	Output Skew ⁽²⁾	—	—	—	—	—	500	ps

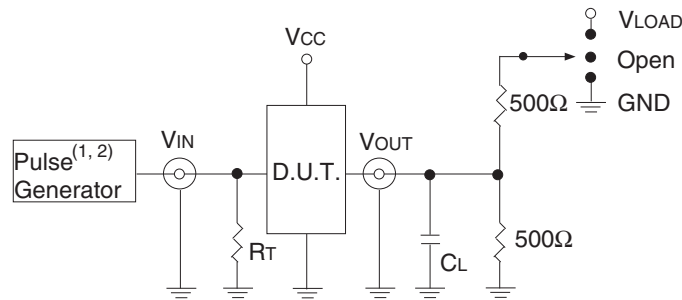
NOTES:

- See TEST CIRCUITS AND WAVEFORMS. $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$.
- Skew between any two outputs of the same package and switching in the same direction.

TEST CIRCUITS AND WAVEFORMS

TEST CONDITIONS

Symbol	V _{CC} ⁽¹⁾ =3.3V±0.3V	V _{CC} ⁽¹⁾ =2.7V	V _{CC} ⁽²⁾ =2.5V±0.2V	Unit
V _{LOAD}	6	6	2 x V _{CC}	V
V _{IH}	2.7	2.7	V _{CC}	V
V _T	1.5	1.5	V _{CC} / 2	V
V _{LZ}	300	300	150	mV
V _{HZ}	300	300	150	mV
C _L	50	50	30	pF



Test Circuit for All Outputs

DEFINITIONS:

C_L = Load capacitance: includes jig and probe capacitance.

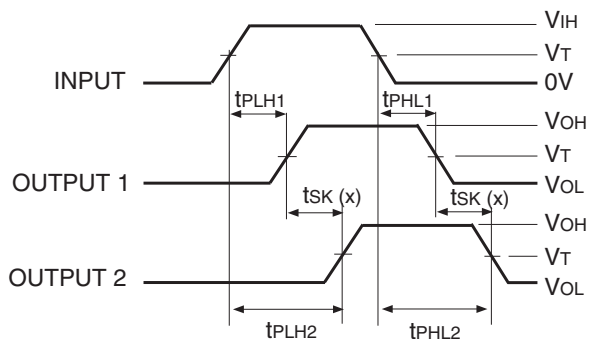
R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

NOTES:

1. Pulse Generator for All Pulses: Rate ≤ 1.0MHz; t_r ≤ 2.5ns; t_r ≤ 2.5ns.
2. Pulse Generator for All Pulses: Rate ≤ 1.0MHz; t_r ≤ 2ns; t_r ≤ 2ns.

SWITCH POSITION

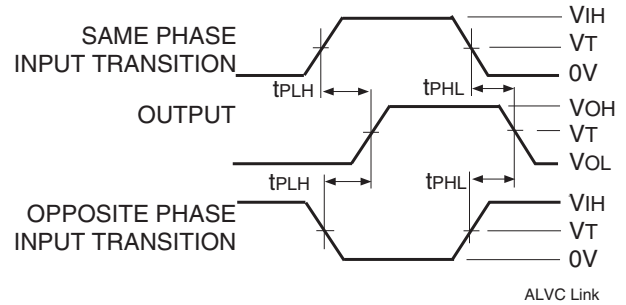
Test	Switch
Open Drain Disable Low Enable Low	V _{LOAD}
Disable High Enable High	GND
All Other Tests	Open



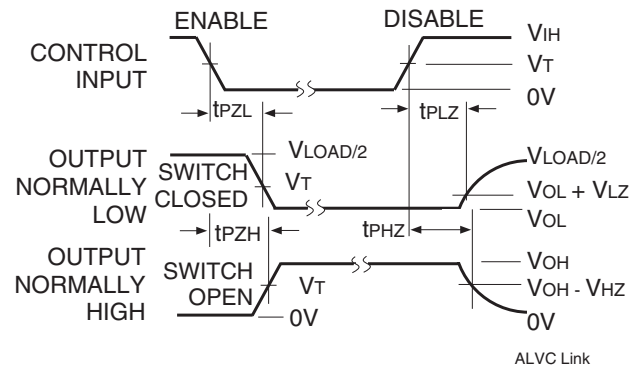
Output Skew - t_{SK(x)}

NOTES:

1. For t_{SK(o)} OUTPUT1 and OUTPUT2 are any two outputs.
2. For t_{SK(b)} OUTPUT1 and OUTPUT2 are in the same bank.



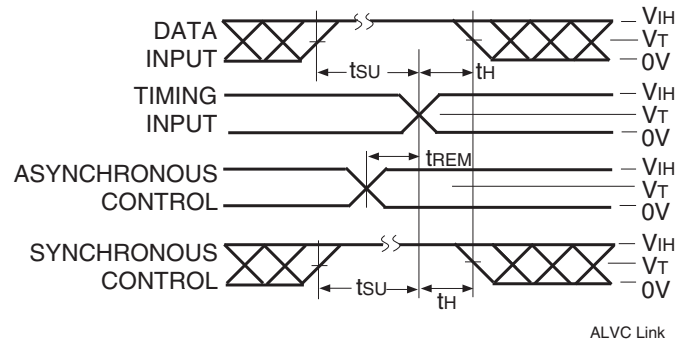
Propagation Delay



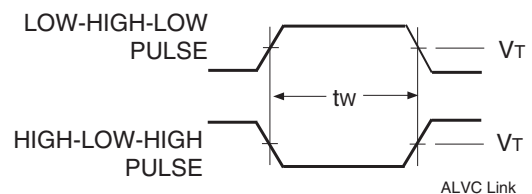
Enable and Disable Times

NOTE:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.



Set-up, Hold, and Release Times



Pulse Width

ORDERING INFORMATION

XX	ALVC	X	XX	XXX	XX	X		
Temp. Range	Bus-Hold	Family	Device Type	Package				
							Blank 8	Tube Tape and Reel
							PAG	Thin Shrink Small Outline Package - Green
							244A	16-Bit Buffer/Driver with 3-State Outputs
							16	Double-Density, $\pm 24\text{mA}$
							Blank	No Bus-Hold
							74	-40°C to $+85^{\circ}\text{C}$

DATASHEET DOCUMENT HISTORY

06/15/2016 Pg. 6 Updated the ordering information by adding Tape and Reel.



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